| | Application Number | 10/587,414 |
|------------------------|------------------------|------------------|
| | Filing Date | 11/7/2006 |
| INFORMATION DISCLOSURE | First Named Inventor | Vincent W. Leung |
| STATEMENT BY APPLICANT | Art Unit | 2817 |
| | Examiner Name | Nguyen, Khanh V. |
| Sheet 1 of 1 | Attorney Docket Number | 0321.72250 |

| UNITED STATES PATENTS | | | | | |
|-----------------------|-------------------------|-----------|----------|--|--|
| Examiner Initials* | Document No. | Dated | Inventor | | |
| /K.N./ | -2003/076474 | 4/24/2003 | Hwang | | |

20030076171



| FOREIGN DOCUMENTS | | | | | | | |
|--------------------|----------------|-----------|---------------------------------|---|--|--|--|
| Examiner Initials* | Document No. | Dated | Inventor | | | | |
| /K.N./ | WO 00/19327 | 4/6/2000 | Actiontec Electronics, Inc. | • | | | |
| /K.N./ | WO 00/45507 | 8/3/2000 | Nortel Networks Corp. | | | | |
| /K.N./ | WO 03/005574 | 1/16/2003 | Koninklijke Philips Electronics | | | | |
| /K.N./ | WO 2004/070970 | 8/19/2004 | Top Global USA, Inc. | · | | | |

| | | NON PATENT LITERATURE DOCUMENTS | |
|-----------------------|-------------|--|-----------------|
| Examiner Initials* | Cite No. | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), city and/or country where published. | T |
| /K.N./ | 1. | VINCENT LEUNG et al., "Digital-IF WCDMA Handset Transmitter IC in 0.25 µm SiGe BiCMOS", Solid-State Circuits Conference 2004, Digest of Technical Papers, ISSCC, 2004, IEEE International, San Francisco, CA Feb. 15-19, 2004, Piscataway, NJ, IEEE, 2/15/2004, pp. 182-191. | |
| /K.N./ | 2. | SHINTARO SHINJO et al., "Low Quiescent Current SiGE HBT Driver Amplifier Having Self Base Bias Control Circuit", IEICE Transactions on Electronics, Vol. E85-C, No. 7, pp. 1404-11., 7/1/2002 | Abstrac only |
| /K.N./ | 3. | TIRDAD SOWLATI et al., "Bias Boosting Technique for a 1.9GHz Class AB RF Amplifier", Low Power Electronics and Design, 2000, Proceedings of the 2000 International Symposium on July 26-27, 2000, Piscataway, NJ. | |